Common Anode Silicon Dual Switching Diodes

These Common Anode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. The DAP222 device is housed in the SC-75/SOT-416 package which is designed for low power surface mount applications, where board space is at a premium. The DAP202U device is housed in the SC-70/SOT-323 package.

Features

- Fast trr
- Low C_D
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	80	Vdc
Peak Reverse Voltage	V_{RM}	80	Vdc
Forward Current	I _F	100	mAdc
Peak Forward Current	I _{FM}	300	mAdc
Peak Forward Surge Current	I _{FSM} (1)	2.0	Adc

THERMAL CHARACTERISTICS

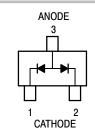
Rating	Symbol	Max	Unit
Power Dissipation	P_{D}	150	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T _{stg}	-55 ~ + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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MARKING DIAGRAMS



SC-70 CASE 419





SC-75 CASE 463 STYLE 4



NB, P9 = Device Codes M = Date Code*

■ = Pb-Free Package (Note: Microdot may be in either location)

*Date Code orientation and/or orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
DAP202UG	SC-70 (Pb-Free)	3000 / Tape & Reel
DAP222G	SC-75 (Pb-Free)	3000 / Tape & Reel
DAP222T1G	SC-75 (Pb-Free)	3000 / Tape & Reel
NSVDAP222T1G	SC-75 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Downloaded from Arrow.com.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I _R	V _R = 70 V	_	0.1	μAdc
Forward Voltage	V _F	I _F = 100 mA	_	1.2	Vdc
Reverse Breakdown Voltage	V_R	I _R = 100 μA	80	_	Vdc
Diode Capacitance	C _D	V _R = 6.0 V, f = 1.0 MHz	_	3.5	pF
Reverse Recovery Time DAP222 DAP202U	t _{rr} (2) t _{tt} (3)	I_F = 5.0 mA, V_R = 6.0 V, R_L = 100 Ω , I_{rr} = 0.1 I_R I_F = 5.0 mA, V_R = 6.0 V, R_L = 50 Ω , I_{rr} = 0.1 I_R	- -	4.0 10.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- t = 1 μS
 t_{rr} Test Circuit for DAP222 in Figure 4.
 trr Test Circuit for DAP202U in Figure 5.

TYPICAL ELECTRICAL CHARACTERISTICS

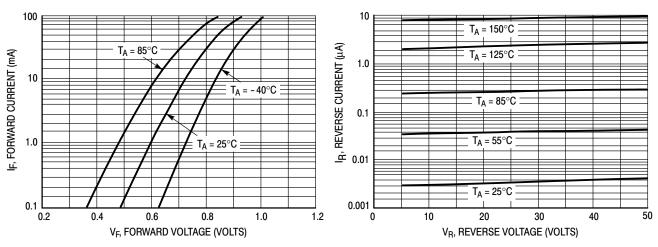


Figure 1. Forward Voltage

Figure 2. Reverse Current

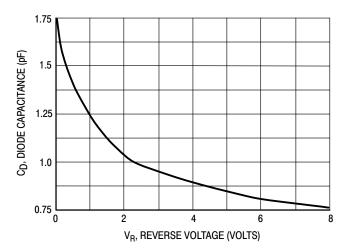


Figure 3. Diode Capacitance

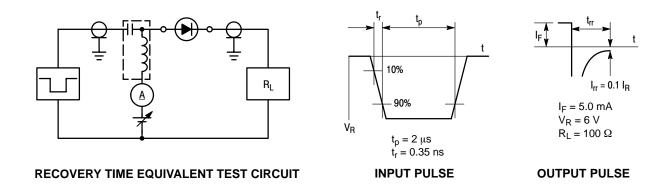


Figure 4. Reverse Recovery Time Test Circuit for the DAP222

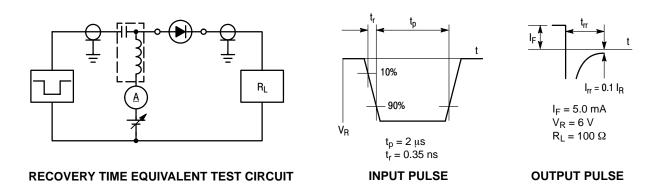
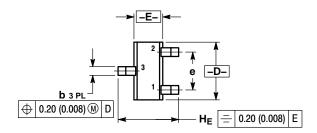


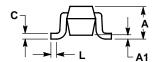
Figure 5. Reverse Recovery Time Test Circuit for the DAP202U

PACKAGE DIMENSIONS

SC-75/SOT-416

CASE 463-01 ISSUE G



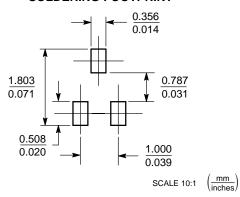


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.70	0.80	0.90	0.027	0.031	0.035	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
b	0.15	0.20	0.30	0.006	0.008	0.012	
С	0.10	0.15	0.25	0.004	0.006	0.010	
D	1.55	1.60	1.65	0.061	0.063	0.065	
E	0.70	0.80	0.90	0.027	0.031	0.035	
е	1.00 BSC			0.04 BSC			
L	0.10	0.15	0.20	0.004	0.006	0.008	
HE	1.50	1.60	1.70	0.060	0.063	0.067	

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

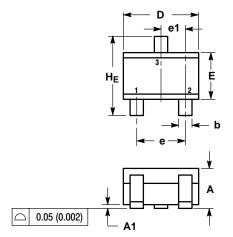
SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

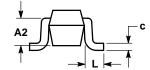
SC-70 (SOT-323) CASE 419-04 ISSUE N



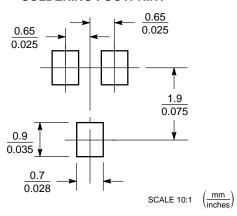
NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2	0.70 REF			0.028 REF			
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.10	2.20	0.071	0.083	0.087	
E	1.15	1.24	1.35	0.045	0.049	0.053	
е	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC			0.026 BSC			
Ĺ	0.20	0.38	0.56	0.008	0.015	0.022	
ΗE	2.00	2.10	2.40	0.079	0.083	0.095	



SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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